Part Number	Customer

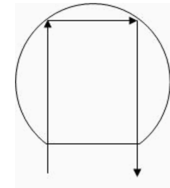
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	WaferVendor
	2.0	Primary Flat Orientation	{110} +/- 1 deg	Wafer Vendor
	3.0	Notch or Flat	semi std / none	Wafer Vendor
	4.0	Overall Thickness	1,000.00 +/- 20.00 um	Guaranteed by Process
	5.0	Total Thickness Variation (TTV)	<5.00um	Guaranteed by Process
	6.0	Bow	<40.00um	Guaranteed by Process
	7.0	Warp	<40.00um	Guaranteed by Process
	8.0	Edge Exclusion	5 mm	Guaranteed by Process
HandleSilicon	9.0	Handle Growth Method	CZ	Wafer Vendor
	10.0	Handle Orientation	<111> off 4 +/- 0.5 degree	Wafer Vendor
	11.0	Handle Thickness	475.00 +/- 15.00 um	Guaranteed by Process
	12.0	Handle Doping Type	N	Wafer Vendor
	13.0	Handle Dopant	Phosphorous	POCl3 deposition (See notes)
	14.0	Handle Resistivity	< 0.0015 Ohmcm	Wafer Vendor
	15.0	Backside Finish	Lapped and etched with no oxide and lasermark	Wafer Vendor
DeviceSilicon	16.0	Device Growth Method	FZ	Wafer Vendor
	17.0	Device Orientation	<111> off 3 .5 +/- 1 degree	Wafer Vendor
	18.0	Nominal Thickness	525.00 +/- 5.00 um	Guaranteed by Process, ADE 1pt 100%
	19.0	Distance to device silicon edge from wafer edge	<= 2mm	Guaranteed by Process
	20.0	Device Doping Type	N	Guaranteed by Process
	21.0	Device Dopant	Phosphorous	Guaranteed by Process
	22.0	Device Resistivity	>5000 Ohmcm	Wafer Vendor
	23.0	Voids	none	Guaranteed by Process, SAM inspection
	24.0	Haze	none	Guaranteed by Process, Bright LIght inspection
	25.0	Scratches	none	Guaranteed by Process, Bright LIght inspection

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

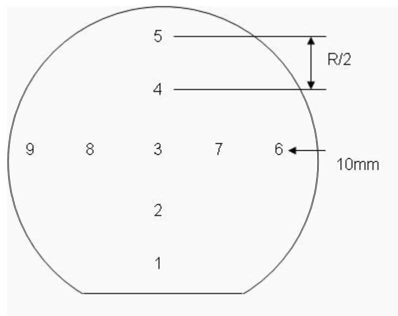
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information